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DS90LV019 3.3V or 5V LVDS Driver/Receiver

National Semiconductor

DS90LV019 3.3V or 5V LVDS Driver/Receiver

General Description

The DS90LV019 is a Driver/Receiver designed specifically for the high speed low power point-to-point interconnect applications. The device operates from a single 3.3V or 5.0V power supply and includes one differential line driver and one receiver. The DS90LV019 features an independent driver and receiver with TTL/CMOS compatibility (D_{IN} and R_{OUT}). The logic interface provides maximum flexibility as 4 separate lines are provided (D_{IN}, DE, $\overline{\text{RE}}$, and R_{OUT}). The device also features a flow-through pin out which allows easy PCB routing for short stubs between its pins and the connector. The driver has 3.5 mA output loop current.

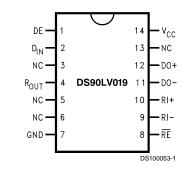
The driver translates between TTL levels (single-ended) to Low Voltage Differential Signaling levels. This allows for high speed operation, while consuming minimal power with reduced EMI. In addition, the differential signaling provides common-mode noise rejection.

The receiver threshold is ± 100 mV over a $\pm 1V$ commonmode range and translates the low swing differential levels to standard (TTL/CMOS) levels.

Features

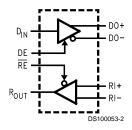
- LVDS Signaling
- 3.3V or 5.0V operation
- Low power CMOS design
- Balanced Output Impedance
- Glitch free power up/down (Driver disabled)
- High Signaling Rate Capacity (above 100 Mbps)
- Ultra Low Power Dissipation
- ±1V Common-Mode Range
- ±100 mV Receiver Sensitivity
- Product offered in SOIC and TSSOP packages
- Flow-Through Pin Out
- Industrial Temperature Range Operation





Order Number DS90LV019TM or DS90LV019TMTC See NS Package Number M14A or MTC14

Block Diagram



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Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Supply Voltage V_{CC}	6.0V			
Enable Input Voltage (DE, RE)	–0.3V to (V _{CC} +0.3V)			
Driver Input Voltage (DIN)	–0.3V to (V _{CC} + 0.3V)			
Receiver Output Voltage				
(R _{OUT})	–0.3V to (V _{CC} + 0.3V)			
Driver Output Voltage (DO±)	-0.3V to +3.9V			
Receiver Input Voltage (RI±)	–0.3V to (V _{CC} + 0.3V)			
Driver Short Circuit Current	Continuous			
ESD (Note 4)				
(HBM, 1.5 kΩ, 100 pF)	> 2.0 kV			
(EIAJ, 0 Ω, 200 pF)	> 200 V			
Maximum Package Power Dissipation at 25°C				
SOIC	960 mW			

Derate SOIC Package	7.7mW/°C
TSSOP	790 mW
Derate TSSOP Package	6.3mW/°C
Storage Temperature Range	−65°C to +150°C
Lead Temperature (Soldering, 4 sec.)	260°C

Recommended Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC}) or	3.0	3.6	V
Supply Voltage (V _{CC})	4.5	5.5	V
Receiver Input Voltage	0.0	2.4	V
Operating Free Air			
Temperature T _A	-40	+85	°C

DC Electrical Characteristics

 $T_A = -40^{\circ}C$ to +85°C unless otherwise noted, $V_{CC} = 3.3 \pm 0.3V$. (Notes 2, 3)

Symbol	Parameter	Conditions		Pin	Min	Тур	Max	Units
DIFFERE	NTIAL DRIVER CHARACTERIS	rics		-				
V _{OD}	Output Differential Voltage	$R_{L} = 100\Omega$ (Figure	e 1)	DO+,	250	350	450	mV
ΔV_{OD}	V _{OD} Magnitude Change	1		DO-		6	60	mV
Vos	Offset Voltage]			1	1.25	1.7	V
ΔV_{OS}	Offset Magnitude Change	1				5	60	mV
I _{ozd}	TRI-STATE [®] Leakage	$V_{OUT} = V_{CC}$ or GI	ND, DE = 0V		-10	±1	+10	μA
I _{OXD}	Power-Off Leakage	V _{OUT} = 3.6V or G	ND, $V_{CC} = 0V$		-10	±1	+10	μA
I _{OSD}	Output Short Circuit Current	$V_{OUT} = 0V, DE =$	V _{cc}		-10	-6	-4	mA
DIFFERE	NTIAL RECEIVER CHARACTER	ISTICS						
V _{OH}	Voltage Output High	VID = +100 mV	I _{OH} = -400 μA	R _{OUT}	2.9	3.3		V
		Inputs Open			2.9	3.3		V
V _{OL}	Voltage Output Low	I _{OL} = 2.0 mA, VID) = -100 mV			0.1	0.4	V
l _{os}	Output Short Circuit Current	$V_{OUT} = 0V$			-75	-34	-20	mA
V _{TH}	Input Threshold High						+100	mV
V _{TH}	Input Threshold Low			RI–	-100			mV
I _{IN}	Input Current	V_{IN} = +2.4V or 0V, V_{CC} = 3.6V or 0V			-10	±1	+10	μA
DEVICE O	HARACTERISTICS							1
V _{IH}	Minimum Input High Voltage			D _{IN} ,	2.0		V _{cc}	V
V _{IL}	Maximum Input Low Voltage			DE, RE	GND		0.8	V
I _{IH}	Input High Current	$V_{IN} = V_{CC} \text{ or } 2.4 V$	/			±1	±10	μA
I _{IL}	Input Low Current	$V_{IN} = GND \text{ or } 0.4$	V			±1	±10	μA
V _{CL}	Input Diode Clamp Voltage	$I_{CLAMP} = -18 \text{ mA}$			-1.5	-0.7		V
I _{CCD}	Power Supply Current	$DE = \overline{RE} = V_{CC}$		V _{cc}		9	12.5	mA
I _{CCR}		$DE = \overline{RE} = 0V$				4.5	7.0	mA
I _{ccz}		$DE = 0V, \overline{RE} = V_{CC}$				3.7	7.0	mA
I _{cc}		$DE = V_{CC}, \overline{RE} = 0$)V			15	20	mA
C _{D output}	Capacitance			DO+, DO-		5		pF
C _{R input}	Capacitance			RI+, RI–		5		pF

Symbol	Parameter	Conditions	Pin	Min	Тур	Max	Units
	NTIAL DRIVER CHARACTERIS		FIII		тур	IVIAA	Units
V _{OD}	Output Differential Voltage	$R_{\perp} = 100\Omega \ (Figure \ 1)$	DO+.	250	360	450	mV
ΔV_{OD}	V _{OD} Magnitude Change		DO-		6	60	mV
V _{os}	Offset Voltage	-		1	1.25	1.8	V
ΔV_{OS}	Offset Magnitude Change	-			5	60	mV
I _{OZD}	TRI-STATE Leakage	$V_{OUT} = V_{CC}$ or GND, DE = 0V	-	-10	±1	+10	μA
I _{OXD}	Power-Off Leakage	$V_{OUT} = 5.5V \text{ or GND}, V_{CC} = 0V$	-	-10	±1	+10	μA
I _{OSD}	Output Short Circuit Current	$V_{OUT} = 0V, DE = V_{CC}$		-10	-6	-4	mA
	NTIAL RECEIVER CHARACTER						<u>I</u>
V _{он}	Voltage High	VID = +100 mV I _{OH} = -400 µA	R _{OUT}	4.3	5.0		V
		Inputs Open		4.3	5.0		V
V _{OL}	Voltage Output Low	I _{OL} = 2.0 mA, VID = -100 mV			0.1	0.4	V
los	Output Short Circuit Current	$V_{OUT} = 0V$		-150	-75	-40	mA
V _{TH}	Input Threshold High		RI+,			+100	mV
V _{TH}	Input Threshold Low		RI–	-100			mV
I _{IN}	Input Current	V_{IN} = +2.4V or 0V, V_{CC} = 5.5V or 0V		-15	±1	+15	μΑ
DEVICE O	HARACTERISTICS						
VIH	Minimum Input High Voltage		D _{IN} ,	2.0		V _{cc}	V
V _{IL}	Maximum Input Low Voltage		DE ,RE	GND		0.8	V
I _{IH}	Input High Current	$V_{IN} = V_{CC} \text{ or } 2.4 \text{ V}$			±1	±10	μA
I _{IL}	Input Low Current	V _{IN} = GND or 0.4V			±1	±10	μA
V _{CL}	Input Diode Clamp Voltage	$I_{CLAMP} = -18 \text{ mA}$		-1.5	-0.8		V
I _{CCD}	Power Supply Current	$DE = \overline{RE} = V_{CC}$	V _{cc}		12	19	mA
I _{CCR}		$DE = \overline{RE} = 0V$			5.8	8	mA
I _{CCZ}		$DE = 0V, \overline{RE} = V_{CC}$			4.5	8.5	mA
I _{cc}		$DE = V_{CC}, \overline{RE} = 0V$			18	48	mA
C _{D output}	Capacitance		DO+, DO–		5		pF
C _{R input}	Capacitance		RI+, RI–		5		pF

Note 1: "Absolute Maximum Ratings" are these beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: All currents into device pins are positive; all currents out of device pins are negative. All voltages are referenced to device ground unless otherwise specified. **Note 3:** All typicals are given for $V_{CC} = +3.3V$ or +5.0V and $T_A = +25^{\circ}C$, unless otherwise stated.

Note 4: ESD Rating:

HBM (1.5 kΩ, 100 pF) > 2.0 kV

EIAJ (0Ω, 200 pF) > 200V.

Note 5: C_L includes probe and fixture capacitance.

Note 6: Generator waveforms for all tests unless otherwise specified; f = 1 MHz, $Z_0 = 50\Omega$, $t_r = t_f \le 6.0$ ns (0%-100%).

AC Electrical Characteristics

 $T_A = -40^{\circ}C$ to +85°C, $V_{CC} = 3.3V \pm 0.3V$. (Note 6)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
DRIVER TIMING REQUIREMENTS						
t _{PHLD}	Differential Propagation Delay High to Low	$R_{L} = 100\Omega,$	2.0	4.0	6.5	ns
t _{PLHD}	Differential Propagation Delay Low to High	C _L = 10 pF	1.0	5.6	7.0	ns
t _{SKD}	Differential Skew t _{PHLD} – t _{PLHD}	(Figure 2 and Figure 3)		0.4	1.0	ns
t _{TLH}	Transition Time Low to High		0.2	0.7	3.0	ns
t _{THL}	Transition Time High to Low		0.2	0.8	3.0	ns

DS90LV019

AC Electrical Characteristics (Continued)

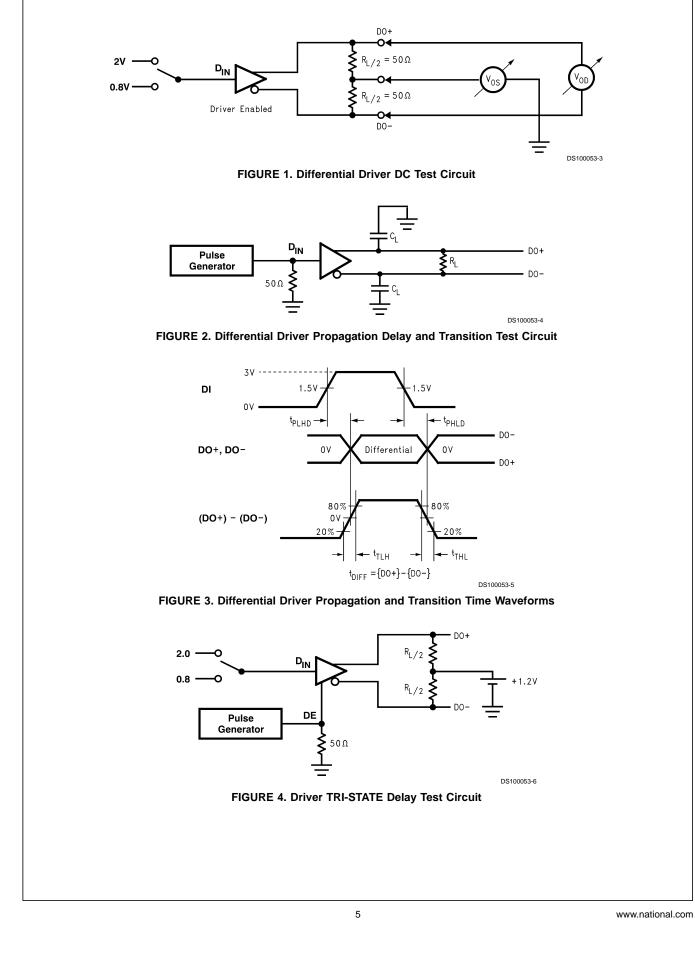
 $T_A = -40^{\circ}C$ to +85°C, $V_{CC} = 3.3V \pm 0.3V$. (Note 6)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
DRIVER T	IMING REQUIREMENTS					
t _{PHZ}	Disable Time High to Z	R _L = 100Ω,	1.5	4.0	8.0	ns
t _{PLZ}	Disable Time Low to Z	C _L = 10 pF	2.5	5.3	9.0	ns
t _{PZH}	Enable Time Z to High	(Figure 4 and Figure 5)	4.0	6.0	8.0	ns
t _{PZL}	Enable Time Z to Low		3.5	6.0	8.0	ns
RECEIVER TIMING REQUIREMENTS						
t _{PHLD}	Differential Propagation Delay High to Low	$C_{L} = 10 \text{ pF},$ VID = 200 mV	3.0	5.8	7.0	ns
t _{PLHD}	Differential Propagation Delay Low to High		3.0	5.6	9.0	ns
t _{SKD}	Differential Skew t _{PHLD} - t _{PLHD}	(Figure 6 and Figure 7)		0.55	1.5	ns
t _r	Rise Time		0.15	2.0	3.0	ns
t _f	Fall Time		0.15	0.9	3.0	ns
t _{PHZ}	Disable Time High to Z	R _L = 500Ω,	3.0	4.0	6.0	ns
t _{PLZ}	Disable Time Low to Z	$C_{L} = 10 \text{ pF}$	3.0	4.5	6.0	ns
t _{PZH}	Enable Time Z to High	(Figure 8 and Figure 9)	3.0	6.0	8.0	ns
t _{PZL}	Enable Time Z to Low		3.0	6.0	8.0	ns

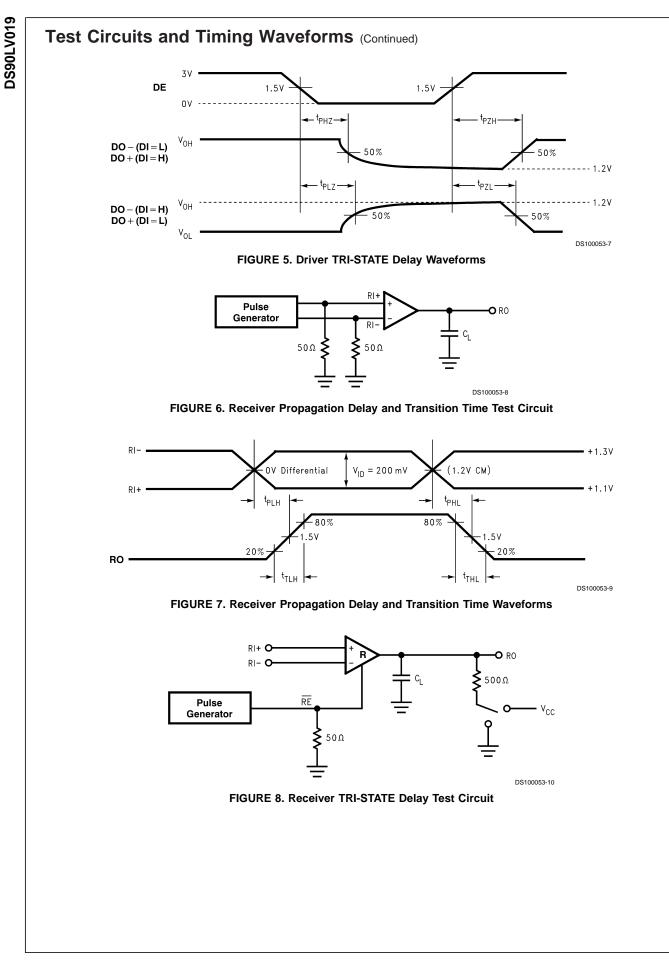
AC Electrical Characteristics

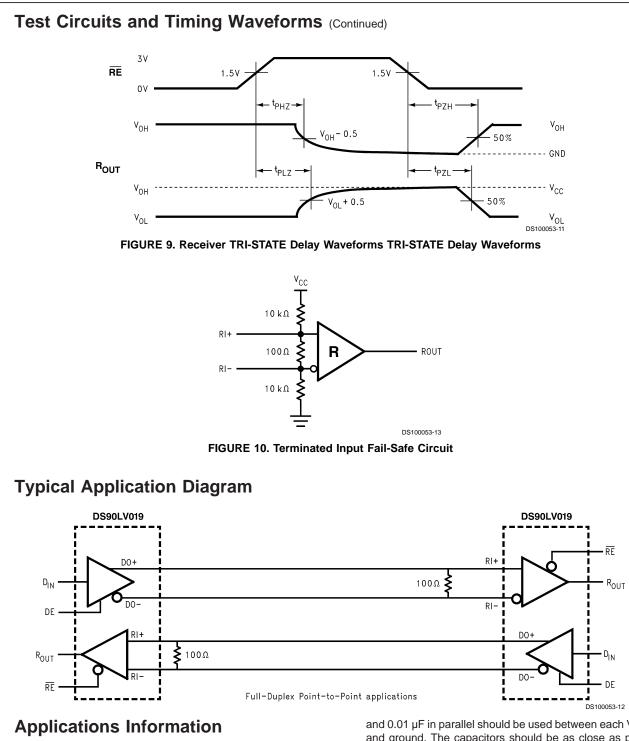
 $T_A = -40^{\circ}C$ to +85°C, $V_{CC} = 5.0V \pm 0.5V$. (Note 6)

	Parameter	Conditions	Min	Tun	Max	Units
Symbol		Conditions	IVIIN	Тур	Wax	Units
DRIVER T	IMING REQUIREMENTS			1		
t _{PHLD}	Differential Propagation Delay High to Low	$R_{L} = 100\Omega,$	2.0	3.3	6.0	ns
t _{PLHD}	Differential Propagation Delay Low to High	$C_L = 10 \text{ pF}$	1.0	3.3	5.0	ns
t _{SKD}	Differential Skew t _{PHLD} – t _{PLHD}	(<i>Figure 2</i> and <i>Figure 3</i>)		0.6	1.0	ns
t _{TLH}	Transition Time Low to High		0.15	0.9	3.0	ns
t _{THL}	Transition Time High to Low		0.15	1.2	3.0	ns
t _{PHZ}	Disable Time High to Z	R _L = 100Ω,	1.5	3.5	7.0	ns
t _{PLZ}	Disable Time Low to Z	C _L = 10 pF	3.0	5.2	9.0	ns
t _{PZH}	Enable Time Z to High	(Figure 4 and Figure 5)	2.0	4.5	7.0	ns
t _{PZL}	Enable Time Z to Low		2.0	4.5	7.0	ns
RECEIVE	R TIMING REQUIREMENTS					
t _{PHLD}	Differential Propagation Delay High to Low	C _L = 10 pF,	3.0	6.0	8.0	ns
t _{PLHD}	Differential Propagation Delay Low to High	VID = 200 mV	3.0	5.6	8.0	ns
t _{SKD}	Differential Skew t _{PHLD} - t _{PLHD}	(<i>Figure 6</i> and <i>Figure 7</i>)		0.7	1.6	ns
t _r	Rise Time		0.15	0.8	3.0	ns
t _f	Fall Time		0.15	0.8	3.0	ns
t _{PHZ}	Disable Time High to Z	$R_{L} = 500\Omega,$	3.0	3.5	4.5	ns
t _{PLZ}	Disable Time Low to Z	$C_L = 10 \text{ pF}$	3.5	3.6	7.0	ns
t _{PZH}	Enable Time Z to High	(<i>Figure 8</i> and <i>Figure 9</i>)	3.0	5.0	7.0	ns
t _{PZL}	Enable Time Z to Low	7	3.0	5.0	7.0	ns



Test Circuits and Timing Waveforms





The DS90LV019 has two control pins, which allows the device to operate as a driver, a receiver or both driver and a receiver at the same time. There are a few common practices which should be implied when designing PCB for LVDS signaling. Recommended practices are:

- Use at least 4 PCB board layer (LVDS signals, ground, power and TTL signals).
- Keep drivers and receivers as close to the (LVDS port side) connector as possible.
- Bypass each LVDS device and also use distributed bulk capacitance. Surface mount capacitors placed close to power and ground pins work best. Two or three multilayer ceramic (MLC) surface mount capacitors 0.1 µF,

and 0.01 μ F in parallel should be used between each V_{CC} and ground. The capacitors should be as close as possible to the $V_{\rm CC}$ pin.

- Use controlled impedance traces which match the differential impedance of your transmission medium (i.e., Cable) and termination resistor.
- Use the termination resistor which best matches the differential impedance of your transmission line.
- Isolate TTL signals from LVDS signals.

MEDIA (CABLE AND CONNECTOR) SELECTION:

Use controlled impedance media. The cables and connectors should have a matched differential impedance of about 100Ω .

Applications Information (Continued)

- Balanced cables (e.g., twisted pair) are usually better than unbalanced cables (ribbon cable, simple coax) for noise reduction and signal quality.
- For cable distances < 0.5m, most cables can be made to work effectively. For distances 0.5m ≤ d ≤ 10m, CAT 3 (category 3) twisted pair cable works well and is readily available and relatively inexpensive. For distances > 10m, and high data rates CAT 5 twisted pair is recommended.
- There are three Fail-Safe scenarios, open input pins, shorted inputs pins and terminated input pins. The first case is guaranteed for DS90LV019. A HIGH state on R_{OUT} pin can be achieved by using two external resistors (one to V_{CC} and one to GND) per *Figure 10* (Terminated Input Fail-Safe Circuit). R1 and R2 should be R_T to limit the loading to the LVDS driver . R_T is selected to match the impedance of the cable.

TABLE 1. Functional Table

MODE SELECTED	DE	RE
DRIVER MODE	Н	Н
RECEIVER MODE	L	L
TRI-STATE MODE	L	Н
FULL DUPLEX MODE	Н	L

TABLE 2. Transmitter Mode

	INPUTS	OUTPUTS		
DE	DI	DO+	DO-	
Н	L	L	Н	
н	Н	Н	L	
н	2 > & > 0.8	Х	Х	
L	Х	Z	Z	

X = High or Low logic state

Z = High impedance state

L = Low state

H = High state

TABLE 3. Receiver Mode

	INPUTS	
RE	(RI+) – (RI–)	
L	L (< -100 mV)	L
L	H (> +100 mV)	Н
L	100 mV > & > -100 mV	Х
Н	Х	Z

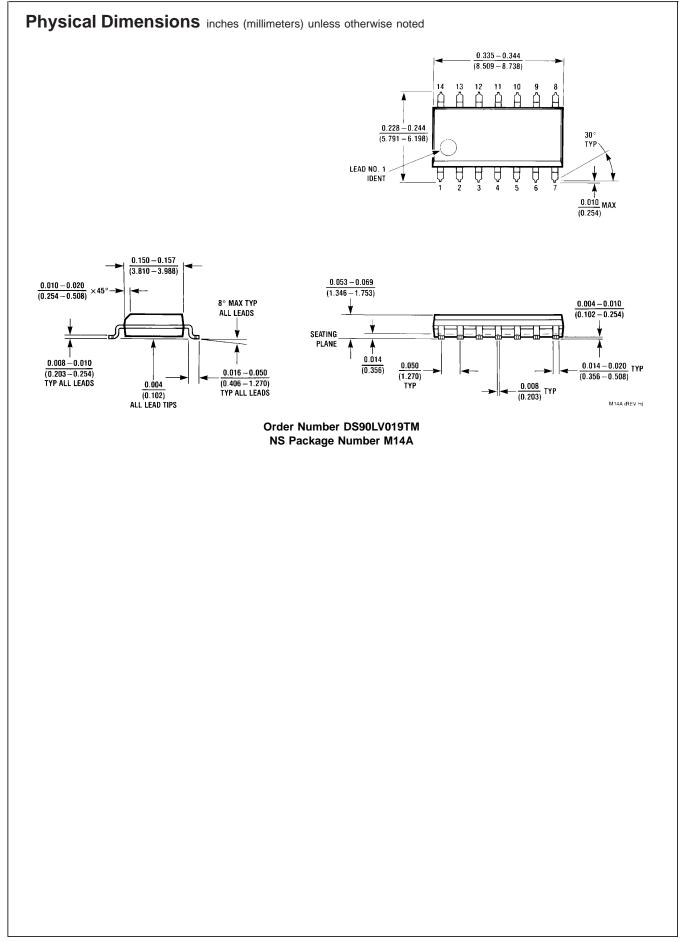
X = High or Low logic state

Z = High impedance state

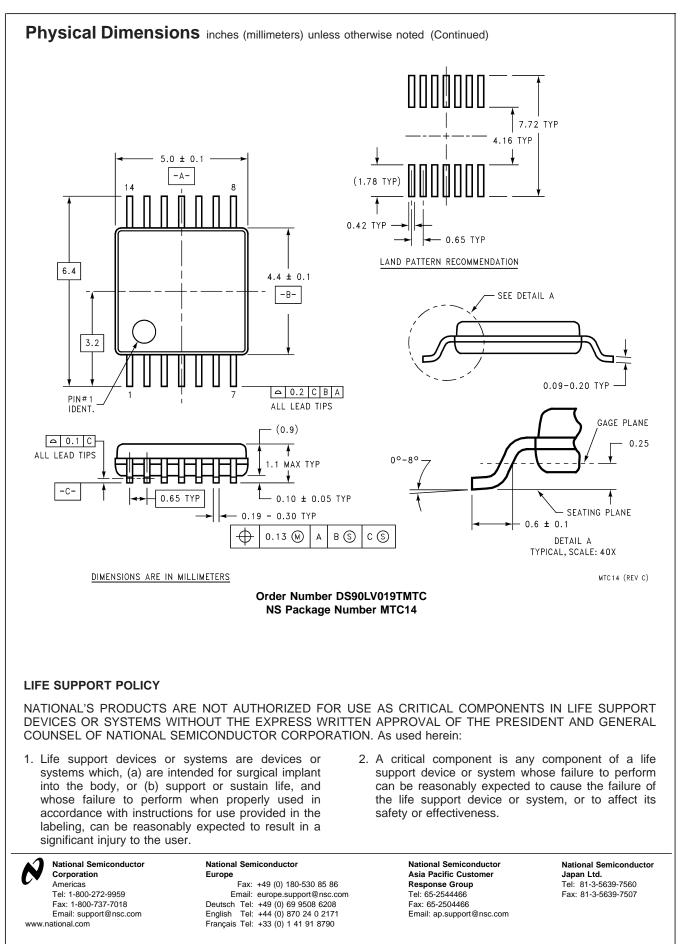
- L = Low state
- H = High state

TABLE 4. Device Pin Description

Pin Name	Pin #	Input/Output	Description
D _{IN}	2	I	TTL Driver Input
DO±	11, 12	0	LVDS Driver Outputs
RI±	9, 10	I	LVDS Receiver Inputs
R _{OUT}	4	0	TTL Receiver Output
RE	8	I	Receiver Enable TTL Input (Active Low)
DE	1	I	Driver Enable TTL Input (Active High)
GND	7	NA	Ground
V _{cc}	14	NA	Power Supply (3.3V \pm 0.3V or 5.0V \pm 0.5V)



DS90LV019



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